

L1200-35M32

Stem type LED with high output power

L1200-35M32 is an InGaAsP LED mounted on a TO-18 stem

with a spherical glass lens being designed for high output power uses.

On forward bias, it emits a spectral band of radiation, which peaks at 1200nm.

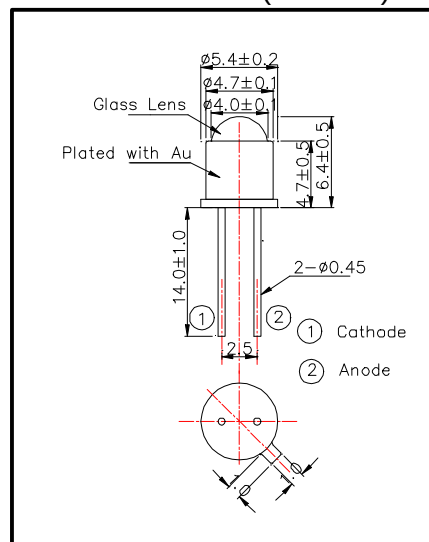
Features

- 1) High radiated intensity
- 2) High Reliability

Specifications

- 1) Product Name NIR LED Lamp
- 2) Type No. L1200-35M32
- 3) Chip Spec.
 - (1) Material InGaAs/InP
 - (2) Peak Wavelength 1200nm
- 4) Package
 - (1) Type TO-18 stem
 - (2) Lens Spherical glass lens
 - (3) Cap Gold plated

Outer dimension(Unit:mm)



Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P _D	120	mW	T _a =25°C
Forward Current	I _F	100	mA	T _a =25°C
Pulse Forward Current	I _{FP}	1000	mA	T _a =25°C
Reverse Voltage	V _R	3	V	T _a =25°C
Operating Temperature	T _{OPR}	-20 ~ +90	°C	
Storage Temperature	T _{STG}	-30 ~ +100	°C	
Soldering Temperature	T _{SOL}	260	°C	

‡ Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

‡ Soldering condition: Soldering condition must be completed within 3 seconds at 260°C

Electro-Optical Characteristics

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F =20mA		0.8	1.3	V
Reverse Current	I _R	V _R =3V			10	uA
Total Radiated Power	P _O	I _F =20mA	0.8	1.8		mW
Peak Wavelength	λ _P	I _F =20mA	1150	1200	1250	nm
Half Width	Δλ	I _F =20mA		100		nm
Viewing Half Angle	Q _{1/2}	I _F =20mA		±15		deg.
Rise Time	t _r	I _F =20mA		10		ns
Fall Time	t _f	I _F =20mA		10		ns

‡ Radiated Power is measured by Ando Optical Multi Meter AQ2140 & AQ2742

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